

Response Under 37 CFR 1.116  
Expedited Procedure  
Examining Group 1753

1. (Currently Amended) A method for manufacturing of a photo mask blank, in particular of a binary photo mask blank, a phase shifting photo mask blank or an extreme ultra violet photo mask blank, comprising the steps of:
  - providing a substrate and a target in a vacuum chamber,
  - providing a first particle beam,
  - sputtering said target by irradiating with said first particle beam,
  - depositing at least a first layer of a first material on said substrate by said sputtering of said target, whereby film stress is optimized to about 0.2 MPa or less by adjusting the angle of incidence of the sputtered target atoms, having a film stress of about 0.2 MPa or less.
- 2.-(Previously Presented) The method of claim 1, wherein said first particle beam is directed onto said target and sputtered particles emerge from said target in direction to said substrate.
3. (Previously Presented) The method of claim 1, wherein at least a second layer of a second material is deposited on said photo mask blank by sputtering of said target.
4. (Previously Presented) The method of claim 1, wherein said target defines a target normal line and said first particle beam hits said target under an angle to said target normal line.
5. (Previously Presented) The method of claim 1, wherein said substrate defines a substrate normal line and sputtered particles from said target hit said photo mask blank under an angle to said substrate normal line.
6. (Currently Amended) ~~The method of claim 1~~ A method for manufacturing of a photo mask blank, comprising the steps of:

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providing a substrate and a target in a vacuum chamber,

providing a first particle beam,

sputtering said target by irradiating with said first particle beam,

depositing at least a first layer of a first material on said substrate by said sputtering

of said target, wherein the rate of depositing of said first layer is between [[0.01]]

0.05 and 5 nm/sec.

7. (Currently Amended) ~~A method for manufacturing of a photo mask blank,~~  
~~comprising the steps of:~~ The method of claim 1, wherein said photo mask blank is  
irradiated by a second particle beam.

~~providing a substrate and a target in a vacuum chamber,~~

~~providing a first particle beam,~~

~~sputtering said target by irradiating with said first particle beam,~~

~~depositing at least a first layer of a first material on said substrate by said~~

~~sputtering of said target, wherein said photo mask blank is irradiated by a second~~  
~~particle beam, and~~

~~wherein a surface of said substrate is cleaned from impurities by irradiating~~  
~~with said second particle beam before said deposition of said first layer, and~~

~~wherein at least one reactive gas is provided in said vacuum chamber at a~~  
~~predetermined pressure and said cleaning is enhanced by said at least one reactive~~  
~~gas.~~

8. (Previously Presented) The method of claim 7, wherein said substrate defines a  
substrate normal line and said second particle beam hits said photo mask blank  
under an angle to said substrate normal line.

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9. (Previously Presented) The method of claim 7, wherein at least one of said first and second particle beam comprises an ion beam.
10. (Previously Presented) The method of claim 7, wherein at least one of said first and second particle beam comprises an ion beam, which is accelerated and focused by an electromagnetic field.
11. (Previously Presented) The method of claim 7 wherein said first and second particle beams are separately controlled for independently depositing layers by said first particle beam and treating at least one of said substrate and said layers by said second particle beam.
12. (Previously Presented) The method of claim 7, wherein said first and second particle beams comprise different particles.
13. (Previously Presented) The method of claim 7, wherein said first and second particle beams have different particle energies.
14. (Previously Presented) The method of claim 7, wherein a surface of said substrate is conditioned by irradiating with said second particle beam.
15. (Canceled)
16. (Canceled)
17. (Previously Presented) The method of claim 7, wherein said at least one reactive gas comprises oxygen.
18. (Previously Presented) The method of claim 7, wherein at least one of the layers is doped by irradiating with said second particle beam.
19. (Previously Presented) The method of claim 18, wherein a plurality of layers is deposited on said photo mask blank and different layers are differently doped.

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20. (Previously Presented) The method of claim 18, wherein at least one of the following parameters:

optical density,  
etch time,  
adhesion and  
reflectance

of at least one of the layers is controlled by said doping.

21. (Previously Presented) The method of claim 7, wherein a surface of at least one of the layers is flattened by irradiating with said second particle beam after the deposition of said at least one layer.

22. (Previously Presented) The method of claim 7 wherein further layers are deposited on said photo mask blank and interface roughness between said layers is reduced by irradiating with said second particle beam.

23. (Previously Presented) The method of claim 7 wherein reflectance of a surface of a reflecting layer is increased by irradiating with said second particle beam.

24. (Previously Presented) The method of claim 1 wherein said first particle beam comprises an ion beam.

25. (Previously Presented) The method of claim 24 wherein said ion beam is a Xenon ion beam.

26. (Previously Presented) The method of claim 25 wherein reflectance of a surface of a reflecting layer is increased by sputtering the target by irradiating with said Xenon ion beam.

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27. (Currently Amended) A method for manufacturing of a photo mask blank,  
comprising the steps of:

providing a substrate and a sputter target in a vacuum chamber,  
providing a deposition particle source and an assist particle source,  
providing a first and second particle beam by means of said deposition and  
assist particle source, respectively,  
sputtering said target by irradiating with said first particle beam, wherein  
said first particle beam is directed from said deposition particle source onto said  
target and sputtered particles emerge from said target in direction to said substrate,  
depositing at least a first layer of a first material on said substrate by said  
sputtering of said target,  
depositing at least a second layer of a second material on said first layer by  
sputtering of said target,  
irradiating said photo mask blank with said second particle beam for  
treating said substrate or at least one of said layers, wherein the reflectance of a  
surface of a reflecting layer is increased by sputtering the target by irradiating with  
a Xenon ion beam. ~~wherein a surface of said substrate is cleaned from impurities by  
irradiating with said second particle beam before said deposition of said first layer,  
and wherein at least one reactive gas is provided in said vacuum chamber at a  
predetermined pressure and said cleaning is enhanced by said at least one reactive  
gas.~~

28. (Canceled)

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29. (Currently Amended) The photo mask blank, obtainable by the method of claim 1 and having a value of film stress of about 0.2 MPa or less.
30. (Currently Amended) A mask blank, comprising  
a substrate and  
one or more layers being deposited on said substrate by ion beam deposition, whereby the photo mask blank with a very low value of film stress of about 0.2 MPa or less, and wherein at least one of said layers has a grain size of 0 nm to 10 nm.
31. (Previously Presented) The mask blank of claim 30, wherein said mask blank is characterized by being treated by irradiating with a second particle beam.
32. (Canceled).
33. (Previously Presented) The mask blank of claim 30, wherein at least one of said layers has a surface roughness of lower than 5 nm rms.
34. (Previously Presented) The mask blank of claim 30, further comprising a light reducing layer.
35. (Previously Presented) The mask blank of claim 30, further comprising an anti-reflective layer.
36. (Currently Amended) A photo mask manufactured from ~~(by a lithography method)~~ of the mask blank of claim 30.
37. (Currently Amended) An apparatus for manufacturing of a mask blank, comprising:  
a vacuum chamber suitable for evacuation and in which a substrate and a target are disposable,

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a deposition particle source for providing a first particle beam which is directable towards said target for sputtering of said target and depositing at least a first layer on said substrate and

an assist particle source for providing a second particle beam which is directable towards said substrate for treating of said substrate and cleaning a surface of said substrate from impurities by irradiating with said second particle beam before said deposition of said first layer, and

means for providing a reactive gas in said vacuum chamber at a predetermined pressure for enhancing said cleaning by said at least one reactive gas, in which the geometrical orientation of the substrate relative to the target, including the angle of incidence of the sputtered target atoms is adjustable to optimize the film stress to about 0.2 MPa.

38. (Previously Presented) The apparatus of claim 37, wherein at least one of said deposition particle source and said assist particle source provide an ion beam.

39. (Previously Presented) The apparatus of claim 37, wherein said deposition particle source provides a first ion beam and said apparatus comprises means for providing an electromagnetic field for accelerating and focusing said first ion beam on its way to said target.

40. (Previously Presented) The apparatus of claim 37, wherein said deposition and assist particle source are separately controllable.

41. (Previously Presented) The apparatus of claim 37, wherein said deposition particle source and said assist particle source are suitable to provide beams of at least one of

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different directions,

different particles, and

different particle energies.

42. (Canceled).

43. (Canceled).

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